



MGBR20S150C

Preliminary

DIODE

DUAL MOS GATED BARRIER RECTIFIER

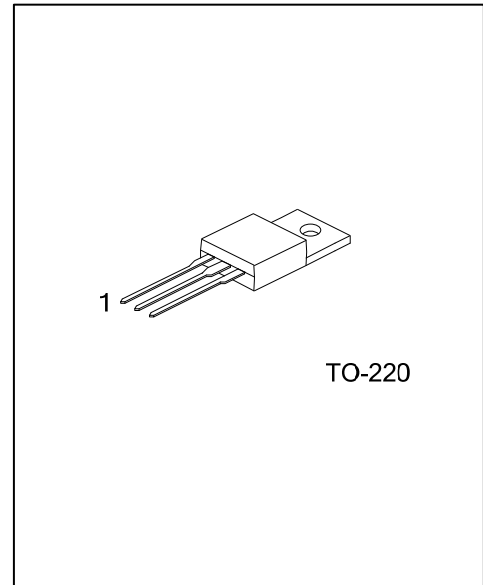
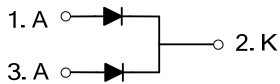
■ DESCRIPTION

The UTC **MGBR20S150C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Super low forward voltage drop
- * High switching speed

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MGBR20S150CL-TA3-T	MGBR20S150CG-TA3-T	TO-220	A	K	A	Tube

Note: Pin Assignment: A: Anode, K: Cathode

<p>MGBR20S150CL-TA3-T</p>	<p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS (PER LEG) ($T_A=25^\circ\text{C}$ unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER SYMBOL		RATINGS	UNIT
DC Blocking Voltage		V_{RM} 150	V
Working Peak Reverse Voltage		V_{RWM} 150	V
Peak Repetitive Reverse Voltage		V_{RRM} 150	V
Average Rectified Output Current Per Device	Per Leg	10 A	
	Total 2	0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I_{FSM} 180	A
Operating Junction Temperature		T_J -65~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG} -65~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (PER LEG) ($T_A=25^\circ\text{C}$ unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	$I_R=0.50\text{mA}$ 150				V
Forward Voltage Drop	V_{FM}	$I_F=10\text{A}$, $T_J=25^\circ\text{C}$			0.80	V
		$I_F=10\text{A}$, $T_J=125^\circ\text{C}$			0.75	V
Leakage Current (Note 1)	I_{RM}	$V_R=150\text{V}$, $T_J=25^\circ\text{C}$			100	μA
		$V_R=150\text{V}$, $T_J=125^\circ\text{C}$			30	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.
2. Thermal resistance junction to case mounted on heatsink.

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